

B5817W SCHOTTKY BARRIER DIODE

FEATURES

Power dissipation

P_D : 450 mW ($T_{amb}=25^\circ\text{C}$)

Collector current

I_F : 1 A

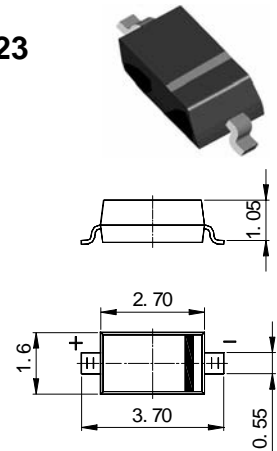
Collector-base voltage

V_R : 20 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^\circ\text{C}$

SOD-123



Unit: mm

MARKING: SJ

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 1\text{mA}$	20		V
Reverse voltage leakage current	I_R	$V_R = 20\text{V}$		1	mA
Forward voltage	V_F	$I_F = 1\text{A}$ $I_F = 3\text{A}$		0.45 0.75	V
Diode capacitance	C_D	$V_R = 4\text{V}, f = 1\text{MHz}$		120	pF